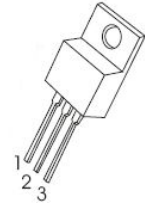


**TIP120,121,122** Darlington TRANSISTOR (NPN)

**TIP125,126,127** Darlington TRANSISTOR (PNP)

**TO-220**

1.BASE  
2.COLLECTOR  
3.EMITTER

**FEATURES**

Medium Power Complementary silicon transistors

**MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)**

Symbol	Parameter	TIP120	TIP121	TIP122	Units
		TIP125	TIP126	TIP127	
V <sub>CBO</sub>	Collector-Base Voltage	60	80	100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	60	80	100	V
V <sub>EBO</sub>	Emitter-Base Voltage	5			V
I <sub>C</sub>	Collector Current -Continuous	5			A
P <sub>C</sub>	Collector Power Dissipation	2			W
R <sub>θJA</sub>	Thermal Resistance Junction to Ambient	62.5			°C/W
R <sub>θJc</sub>	Thermal Resistance Junction to Case	1.92			°C/W
T <sub>J</sub>	Junction Temperature	150			°C
T <sub>stg</sub>	Storage Temperature	-55to+150			°C

**ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
<b>Collector-base breakdown voltage</b> TIP120,TIP125 TIP121,TIP126 TIP122,TIP127	V(BR) <sub>CBO</sub>	I <sub>C</sub> = 1mA, I <sub>E</sub> =0	60 80 100		V
<b>Collector-emitter breakdown voltage</b> TIP120,TIP125 TIP121,TIP126 TIP122,TIP127	V <sub>CEO(SUS)</sub>	I <sub>C</sub> = 30mA, I <sub>B</sub> =0	60 80 100		V
<b>Collector cut-off current</b> TIP120,TIP125 TIP121,TIP126 TIP122,TIP127	I <sub>CBO</sub>	V <sub>CB</sub> = 60 V, I <sub>E</sub> =0 V <sub>CB</sub> = 80 V, I <sub>E</sub> =0 V <sub>CB</sub> = 100V, I <sub>E</sub> =0		0.2	mA
<b>Collector cut-off current</b> TIP120,TIP125 TIP121,TIP126 TIP122,TIP127	I <sub>CEO</sub>	V <sub>CE</sub> =30 V, I <sub>B</sub> =0 V <sub>CE</sub> =40 V, I <sub>B</sub> =0 V <sub>CE</sub> =50 V, I <sub>B</sub> =0		0.5	mA
<b>Emitter cut-off current</b>	I <sub>EBO</sub>	V <sub>EB</sub> =5 V, I <sub>C</sub> =0		2	mA
<b>DC current gain</b>	h <sub>FE(1)</sub>	V <sub>CE</sub> = 3V, I <sub>C</sub> =0.5A	1000		
	h <sub>FE(2)</sub>	V <sub>CE</sub> = 3V, I <sub>C</sub> =3 A	1000		
<b>Collector-emitter saturation voltage</b>	V <sub>CE(sat)</sub>	I <sub>C</sub> =3A, I <sub>B</sub> =12mA I <sub>C</sub> =5 A, I <sub>B</sub> =20mA		2 4	V
<b>Base-emitter voltage</b>	V <sub>BE</sub>	V <sub>CE</sub> =3V, I <sub>C</sub> =3 A		2.5	V
<b>Output Capacitance</b> TIP125,TIP126,TIP127 TIP120,TIP121,TIP122	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=0.1MHz		300 200	pF

## Typical Characteristics

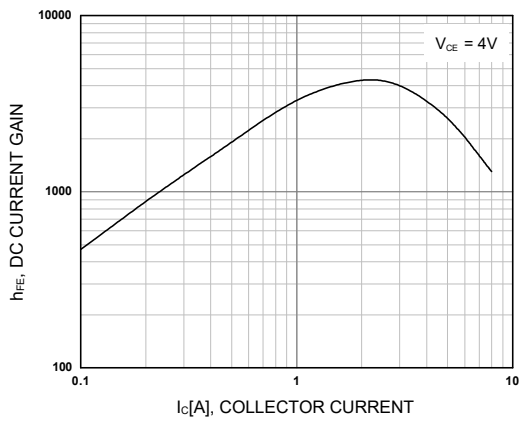


Figure 1. DC current Gain

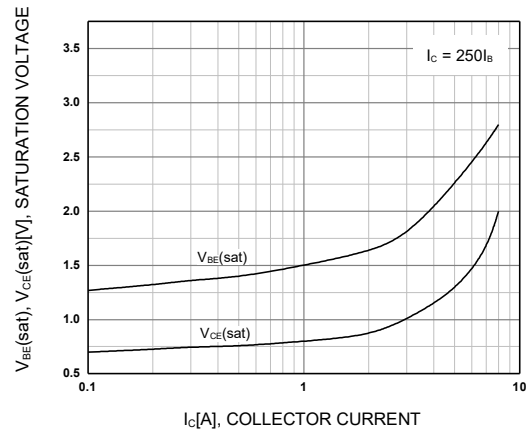


Figure 2. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

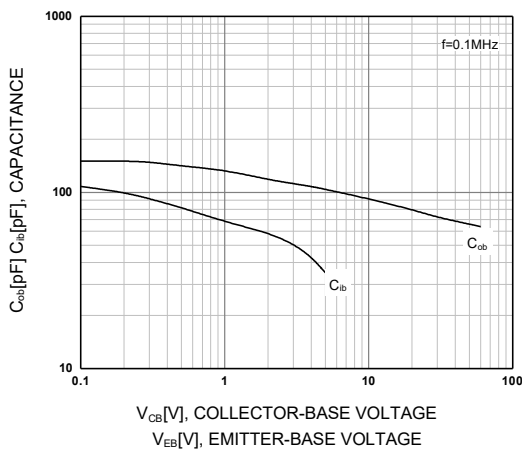


Figure 3. Output and Input Capacitance  
vs. Reverse Voltage

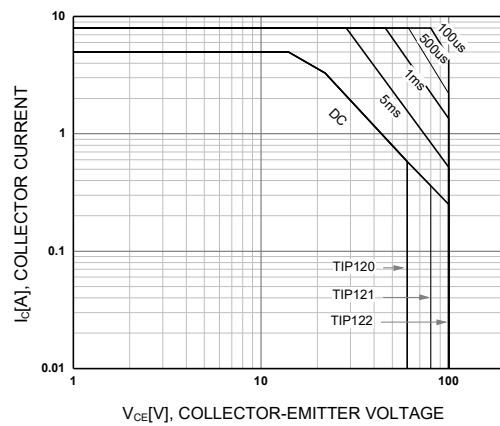


Figure 4. Safe Operating Area

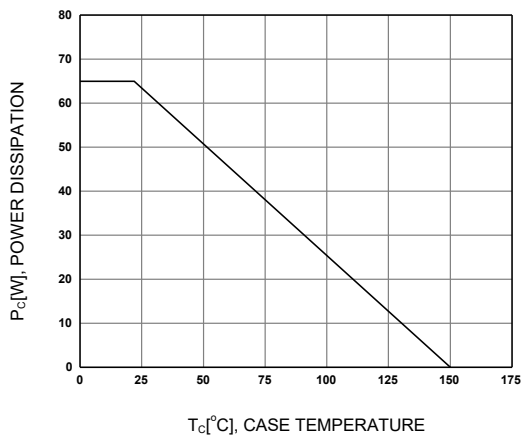


Figure 5. Power Derating